

BUT11A HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

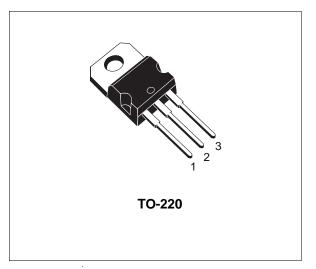
- STMicroelectronics PREFERRED SALESTYPE
- NPN TRANSISTOR
- HIGH VOLTAGE CAPABILITY
- FAST SWITCHING SPEED

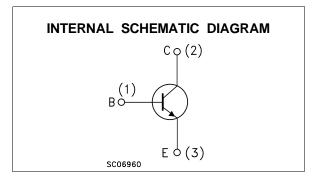
APPLICATIONS:

 FLYBACK AND FORWARD SINGLE TRANSISTOR LOW POWER CONVERTERS

DESCRIPTION

The BUT11A is a silicon Multiepitaxial Mesa NPN transistor in Jedec TO-220 plastic package, particularly intended for switching application.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V _{CES}	Collector-Emitter Voltage (V _{BE} = 0 V)	1000	V	
Vceo	Collector-Emitter Voltage $(I_B = 0)$	450	V	
Vebo	Emitter-Base Voltage $(I_C = 0)$	9	V	
Ιc	Collector Current	5	A	
Ісм	Collector Peak Current (t _p < 5 ms)	10	A	
IB	Base Current	2	A	
I _{BM}	Base Peak Current (t _p < 5 ms)	4	A	
Ptot	Total Power Dissipation at $T_c \le 25$ °C	83	W	
T _{stg}	Storage Temperature	-65 to 150	°C	
Tj	Max. Operating Junction Temperature	150	°C	

THERMAL DATA

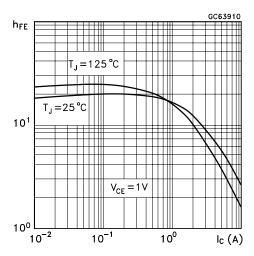
R _{thj-case}	Thermal Resistance Junction-case	Max	1.5	°C/W	1
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Symbol	Parameter	Tes	t Conditions	Min.	Тур.	Max.	Unit
ICES	Collector Cut-off Current (V _{BE} = 0)	V_{CE} = rated V at T _c = 125°C				1 2	mA mA
I _{EBO}	Emitter Cut-off Current $(I_C = 0)$	I _C = 0	$V_{BE} = 9 V$			10	mA
$V_{\text{CEO}(\text{sus})^{\star}}$	Collector-emitter Sustaining Voltage (I _B = 0)	$I_{B (off)} = 0$	I _C = 100 mA	450			V
V _{CE(sat)*}	Collector-emitter Saturation Voltage	I _C = 2.5 A	I _B = 0.5 A			1.5	V
V _{BE(sat)*}	Base-emitter Saturation Voltage	I _C = 2.5 A	I _B = 0.5 A			1.3	V
hfe	DC Current Gain	I _C = 5 mA I _C = 0.5 A		10 10		35 35	
t _{on} t _s t _f	RESISTIVE LOAD Turn on Time Storage Time Fall Time	$I_{\rm C} = 2.5 \text{ A}$ $I_{\rm B} = -I_{\rm B2} = 0.5$				1 4 0.8	μs μs μs

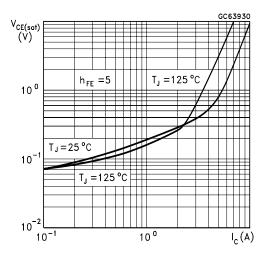
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

* Pulsed: Pulse duration = $300 \,\mu$ s, duty cycle 1.5 %.

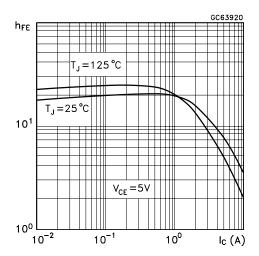
DC Current Gain



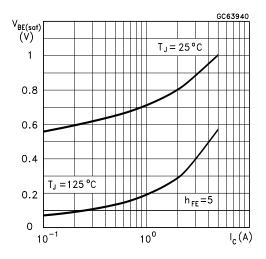
Collector-Emitter Saturation Voltage



DC Current Gain



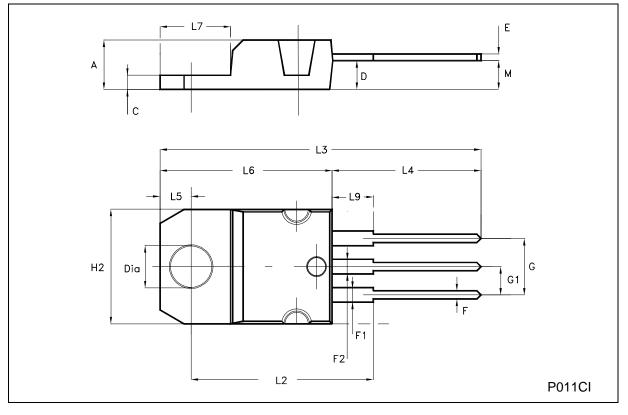
Base-Emitter Saturation Voltage



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TO-220 MECHANICAL DATA

DIM	mm			inch			
DIM.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	4.40		4.60	0.173		0.181	
С	1.23		1.32	0.048		0.052	
D	2.40		2.72	0.094		0.107	
E	0.49		0.70	0.019		0.027	
F	0.61		0.88	0.024		0.034	
F1	1.14		1.70	0.044		0.067	
F2	1.14		1.70	0.044		0.067	
G	4.95		5.15	0.194		0.202	
G1	2.40		2.70	0.094		0.106	
H2	10.00		10.40	0.394		0.409	
L2		16.40			0.645		
L4	13.00		14.00	0.511		0.551	
L5	2.65		2.95	0.104		0.116	
L6	15.25		15.75	0.600		0.620	
L7	6.20		6.60	0.244		0.260	
L9	3.50		3.93	0.137		0.154	
М		2.60			0.102		
DIA.	3.75		3.85	0.147		0.151	



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